

Supporting Information

Ternary polymer solar cells: Impact of non-fullerene acceptors on optical and morphological properties

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Chemical name of donor material:

P3HT poly(3-hexylthiophene-2,5-diyl)

Chemical name of acceptor materials:

PC₆₁BM [6,6]-phenyl-C₆₁-butyric-acid-methyl ester

ITIC 3,9-bis(2-methylene-(3-(1,1-dicyanomethylene)-indanone))-5,5,11,11-tetrakis(4-hexylphenyl)-dithieno[2,3-d:2',3'-d']-s-indaceno[1,2-b:5,6-b']dithiophene

eh-IDTBR (5Z)-3-ethyl-2-sulfanylidene-5- [[4-[9,9,18,18-tetrakis(2-ethylhexyl)-15-[7-[(Z)-(3-ethyl-4-oxo-2-sulfanylidene-1,3-thiazolidin-5-ylidene)methyl]-2,1,3-benzothiadiazol-4-yl]-5,14-dithiapentacyclo[10.6.0.0^{3,10}.0^{4,8}.0^{13,17}]octadeca-1(12),2,4(8),6,10,13(17),15-heptaen-6-yl]-2,1,3-benzothiadiazol-7-yl]methylidene]-1,3-thiazolidin-4-one

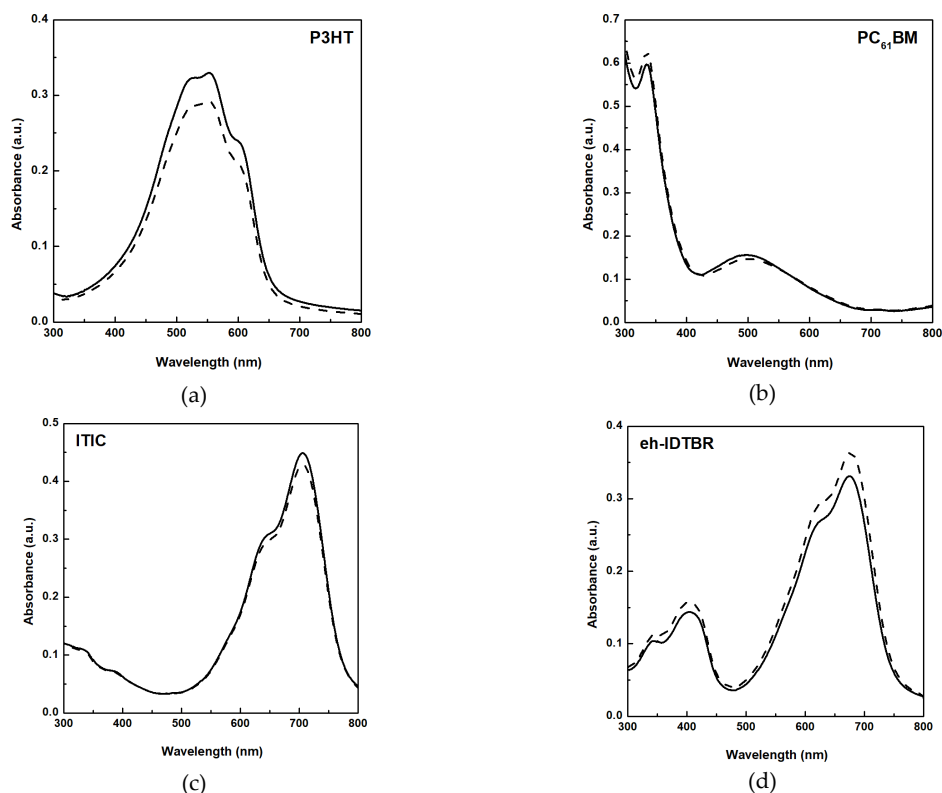


Figure S1: Absorption spectra of neat films depending on annealing temperature (100°C in dotted line and 140°C in solid-line): P3HT (a), PC₆₁BM (b), ITIC (c) and eh-IDTBR (d).

Table S1: Intensity and wavelength of maximum absorption peaks (from Figure S1) for neat films of P3HT, PC₆₁BM, ITIC and eh-IDTBR.

	100°C		140°C		Abs.(140°C)/Abs.(100°C)
	Abs.	λ (nm)	Abs.	λ (nm)	
P3HT	0.29	552	0.33	552	1.13
PC ₆₁ BM	0.14	499	0.15	500	1.07
ITIC	0.43	706	0.44	706	1.02
eh-IDTBR	0.36	677	0.33	674	0.91

For eh-IDTBR, the absorption spectrum at 100°C is more intense than that at 140°C with $\text{Abs.}(140^\circ\text{C})/\text{Abs.}(100^\circ\text{C})=0.91$. This increase reflects a specific change in the orientation of the molecules induced by thermal annealing. 2D-GIXRD measurements on eh-IDTBR films annealed at 100°C and 140°C provide explanations (Figure S7). At 100°C, the intense (010) diffraction peak in out-of-profile (q_z) strengthens the face-on orientation of eh-IDTBR molecules, which increases the surface area absorbing the photons, and consequently the absorption intensity in Figure S1d. At 140°C, the emergence of an intense, narrow diffraction peak indexed (100) and its replicas (200) and (300) in q_z profile highlights a very significant change in the orientation of the molecules, from face-on orientation to edge-on, reducing the surface area for photon absorption. With a $\text{Abs.}(140^\circ\text{C})/\text{Abs.}(100^\circ\text{C})=1.02$, no significant impact of thermal annealing is observe for ITIC films.

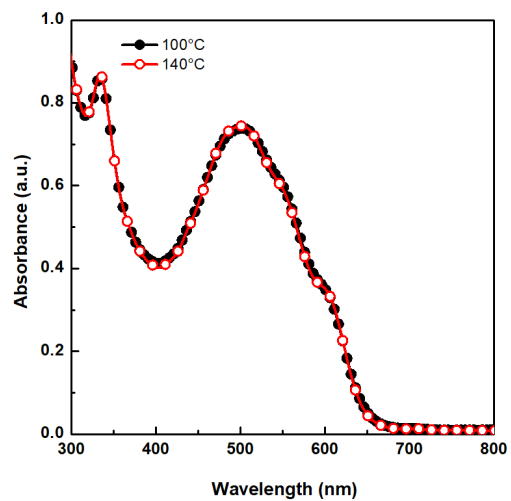


Figure S2: Absorption spectra of binary P3HT:PC₆₁BM films depending on annealing temperature (100°C and 140°C). In these non-normalized spectra, the fullerene peak at 335 nm is unaffected by blend annealing, so the absorption spectra of ternary mixtures in Figures 2c and 2d can be normalized to this peak.

Table S2: Electron and hole mobility values determinate by SCLC protocol for electron-only and hole-only devices based on P3HT, P3HT:PC₆₁BM, P3HT:PC₆₁BM:ITIC and P3HT:PC₆₁BM:eh-IDTBR layers as function of thermal annealing temperature (100°C or 140°C). The thickness of each layer is indicated as required for the SCLC protocol. The average values (μ_{average}) of the mobilities were taken to produce the Figure 7.

		P3HT		P3HT:PC ₆₁ BM		P3HT:PC ₆₁ BM:ITIC		P3HT:PC ₆₁ BM:eh-IDTBR	
electrons	Temperature			100°C	140°C	100°C	140°C	100°C	140°C
	Tickness (nm)			206	220	174	191	173	195
	μ_{average} (cm ² .V ⁻¹ .s ⁻¹)			1.26.10 ⁻⁸	1.27.10 ⁻⁵	1.77.10 ⁻⁵	1.99.10 ⁻⁴	7.86.10 ⁻⁶	4.13.10 ⁻⁴
	Standard deviation			1.51.10 ⁻⁸	1.25.10 ⁻⁵	1.97.10 ⁻⁵	9.09.10 ⁻⁵	4.75.10 ⁻⁶	1.10.10 ⁻⁴
	μ_{min} (cm ² .V ⁻¹ .s ⁻¹)			1.03.10 ⁻¹⁰	6.31.10 ⁻⁶	2.41.10 ⁻⁶	1.03.10 ⁻⁴	1.71.10 ⁻⁶	2.37.10 ⁻⁴
	μ_{max} (cm ² .V ⁻¹ .s ⁻¹)			6.10.10 ⁻⁸	7.75.10 ⁻⁵	6.58.10 ⁻⁵	3.76.10 ⁻⁴	1.99.10 ⁻⁵	6.13.10 ⁻⁴
holes	Temperature (°C)	100°C	140°C	100°C	140°C	100°C	140°C	100°C	140°C
	Tickness (nm)	92	101	194	199	187	198	200	198
	μ_{average} (cm ² .V ⁻¹ .s ⁻¹)	2.73.10 ⁻⁴	2.35.10 ⁻⁴	1.06.10 ⁻³	2.17.10 ⁻³	2.20.10 ⁻⁵	5.14.10 ⁻³	6.49.10 ⁻⁴	6.43.10 ⁻³
	Standard deviation	6.45.10 ⁻⁶	5.90.10 ⁻⁶	6.66.10 ⁻⁶	4.86.10 ⁻⁵	9.07.10 ⁻⁸	2.05.10 ⁻⁵	1.01.10 ⁻⁶	3.38.10 ⁻⁵
	μ_{min} (cm ² .V ⁻¹ .s ⁻¹)	1.43.10 ⁻⁴	1.62.10 ⁻⁴	9.06.10 ⁻⁴	1.51.10 ⁻³	1.58.10 ⁻⁵	3.77.10 ⁻³	4.93.10 ⁻⁴	4.40.10 ⁻³
	μ_{max} (cm ² .V ⁻¹ .s ⁻¹)	3.69.10 ⁻⁴	3.15.10 ⁻⁴	1.23.10 ⁻³	3.02.10 ⁻³	2.71.10 ⁻⁵	6.49.10 ⁻³	7.97.10 ⁻⁴	8.04.10 ⁻³

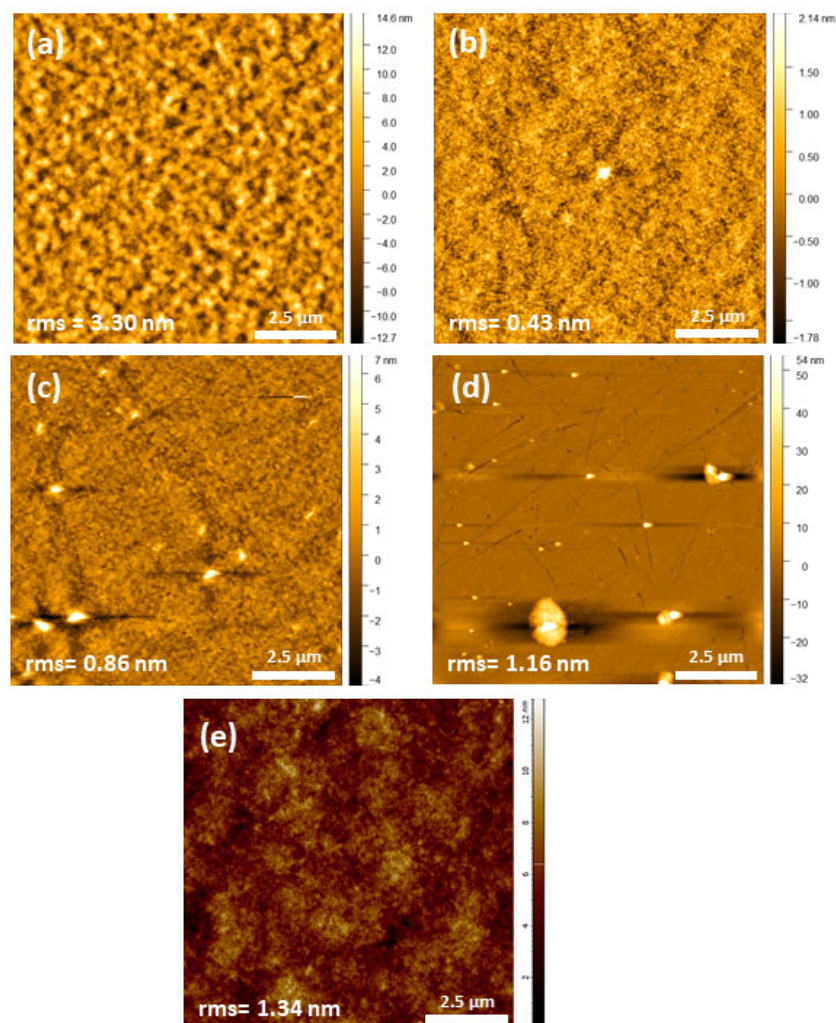


Figure S3: AFM images of neat P3HT (a), PC₆₁BM (b), ITIC (c), eh-IDTBR (d) films and ternary P3HT:PC₆₁BM:ITIC blend (e) thermal annealed at 140°C. Size of micrographies: 10 × 10 μm².

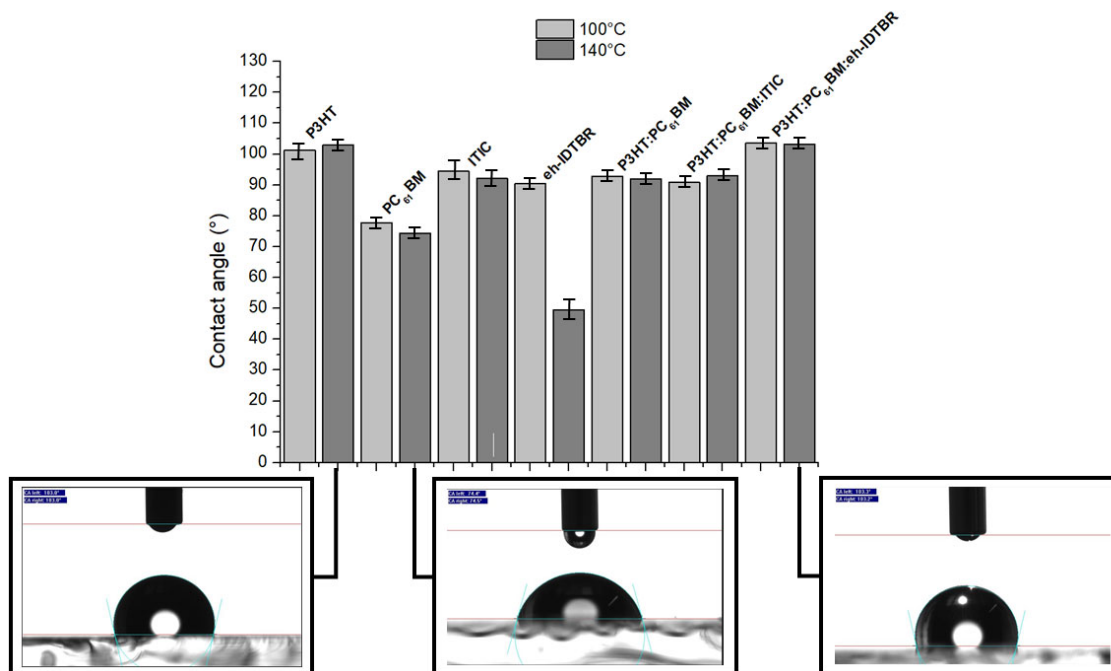


Figure S4: Graph showing water contact angle on neat films (P3HT, PC₆₁BM, ITIC and eh-IDTBR), binary (P3HT:PC₆₁BM) and ternary (P3HT:PC₆₁BM:ITIC and P3HT:PC₆₁BM:eh-IDTBR) blends as function of thermal annealing temperature (100°C and 140°C). Corresponding images for P3HT, PC₆₁BM and P3HT:PC₆₁BM:eh-IDTBR at 140°C.

When the substrate consists of two kinds of species, the Cassie-Baxter equation [1,2] obtains the form:

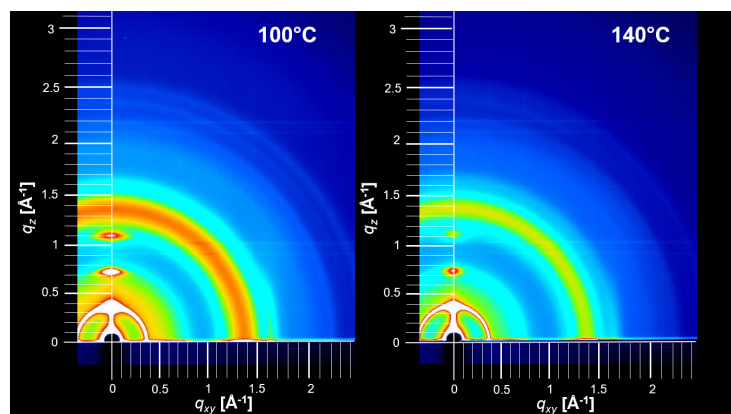
$$\cos\theta = f_1 \cos\theta_1 + f_2 \cos\theta_2$$

where θ is the WCA measured on the surface composed of the two compounds (compound 1 and compound 2), θ_1 is the WCA measured on the surface composed of compound 1 and θ_2 is the WCA measured on the surface composed of compound 2. f_1 and f_2 are the fraction of compound 1 and compound 2.

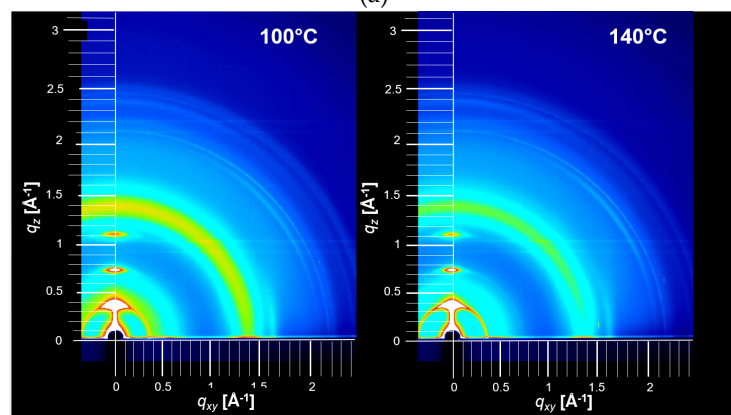
In the case of the binary P3HT:PC₆₁BM blend, f_{P3HT} and f_{PC61BM} are 0.48 and 0.52 at 100°C; and 0.88 and 0.12 at 140°C.

[1] Cassie A. B. D.; Baxter S., Wettability of porous surfaces, Trans. Faraday Soc. 1944, 40, 546 – 551.

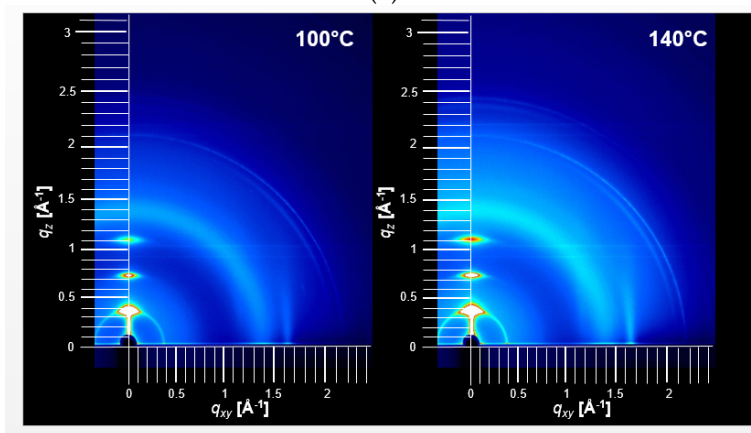
[2] Cassie A. B. D. Contact angles, Discuss. Faraday Soc., 1948, 3, 11 – 16.



(a)



(b)



(c)

Figure S5: 2D-GIXRD patterns of P3HT:PC₆₁BM (a), P3HT:PC₆₁BM:ITIC (b) and P3HT:PC₆₁:eh-IDTBR (c) blends as function of thermal annealing temperature.

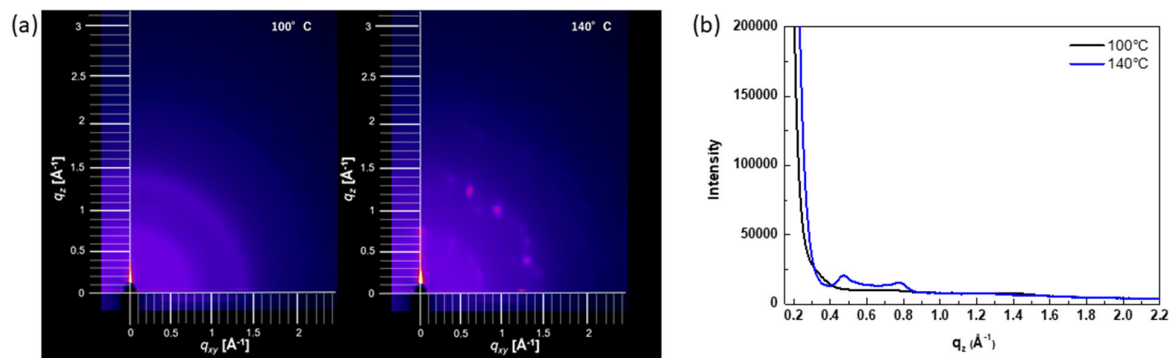


Figure S6: 2D-GIXRD patterns (a) and corresponding out of plane profiles (b) of PC₆₁BM layers as function of thermal annealing temperature.

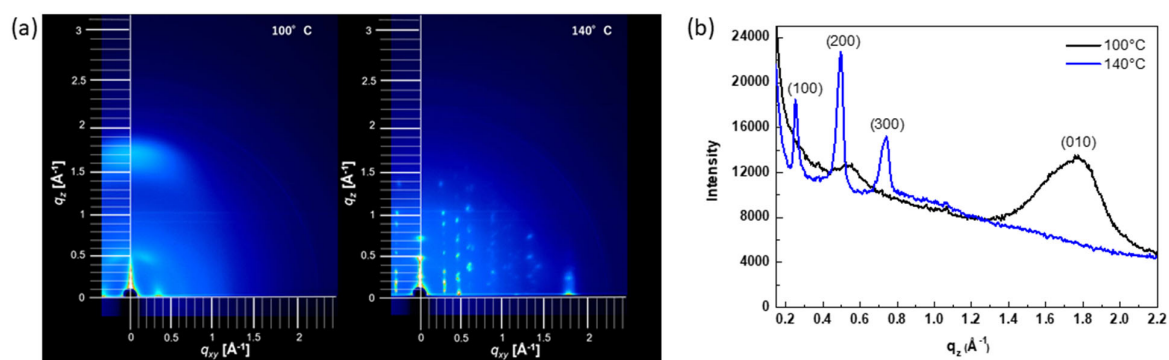


Figure S7: 2D-GIXRD patterns (a) and corresponding out of plane profiles (b) of eh-IDTBR layers as function of thermal annealing temperature.

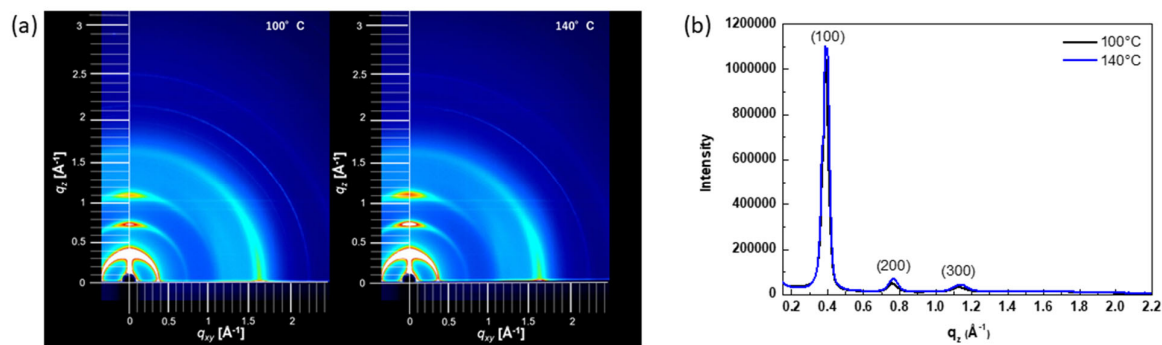


Figure S8: 2D-GIXRD patterns (a) and corresponding out of plane profiles (b) of P3HT layers as function of thermal annealing temperature.

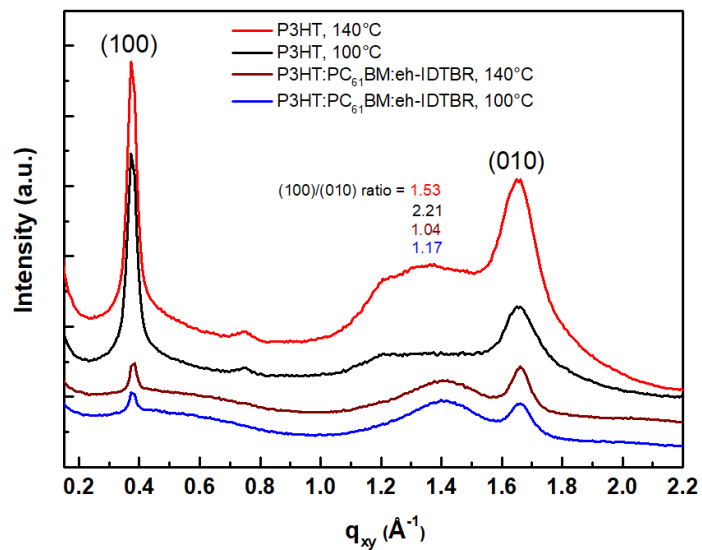


Figure S9: In plane profiles of P3HT and P3HT:PC₆₁BM:eh-IDTBR layers as function of thermal annealing temperature. Ratio of (100)/(010) peak intensities is given to evaluate the evolution ratio between edge-on and face-on orientation of P3HT polymer chain.